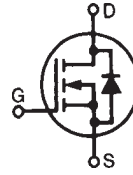


Linear L2™ Power MOSFET with extended FBSOA

IXTH30N60L2
IXTQ30N60L2
IXTT30N60L2

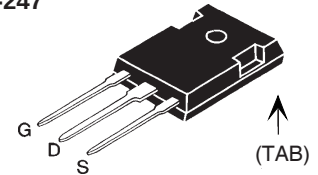
$V_{DSS} = 600V$
 $I_{D25} = 30A$
 $R_{DS(on)} \leq 240m\Omega$

N-Channel Enhancement Mode
Avalanche rated

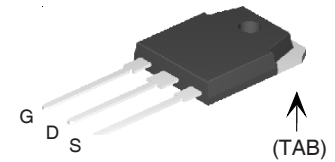


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	600	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	30	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	80	A
I_A	$T_C = 25^\circ C$	30	A
E_{AS}	$T_C = 25^\circ C$	2	J
P_D	$T_C = 25^\circ C$	540	W
T_J		-55 to +150	$^\circ C$
T_{JM}		+150	$^\circ C$
T_{stg}		-55 to +150	$^\circ C$
T_L	1.6mm (0.063in) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10s	260	$^\circ C$
M_d	Mounting torque (TO-247&TO-3P)	1.13/10	Nm/lb.in.
Weight	TO-247	6.0	g
	TO-3P	5.5	g
	TO-268	4.0	g

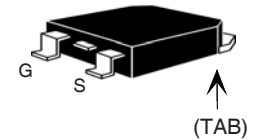
TO-247



TO-3P



TO-268



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$			50 μA
	$V_{GS} = 0V$ $T_J = 125^\circ C$			300 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			240 m Ω

Features

- Designed for linear operation
- International standard packages
- Avalanche rated
- Molding epoxies meet UL 94 V-0 flammability classification
- Guaranteed FBSOA at $75^\circ C$

Applications

- Solid state circuit breakers
- Soft start controls
- Linear amplifiers
- Programmable loads
- Current regulators

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10V, I_D = 0.5 \cdot I_{D25}, \text{ Note 1}$	10	14	18
C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		10.7	nF
C_{oss}			600	pF
C_{rss}			130	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega \text{ (External)}$		43	ns
t_r			65	ns
$t_{d(off)}$			123	ns
t_f			43	ns
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		335	nC
Q_{gs}			58	nC
Q_{gd}			212	nC
R_{thJC}	(TO-247&TO-3P)			0.23 °C/W
R_{thCS}		0.25		°C/W

Safe Operating Area Specification

Symbol	Test Conditions	Min.	Typ.	Max.
SOA	$V_{DS} = 480V, I_D = 0.6A, T_C = 75^\circ C, t_p = 3s$	288		W

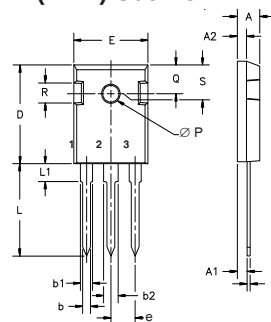
Source-Drain Diode

Characteristic Values
($T_J = 25^\circ C$, unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0V$			30 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			120 A
V_{SD}	$I_F = I_S, V_{GS} = 0V, \text{ Note 1}$			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100A/\mu s, V_R = 100V$		710	ns

Note 1: Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.

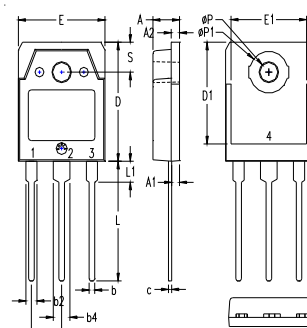
TO-247 (IXTH) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter	Inches
	Min. Max.	Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L1	4.50	.177
ØP	3.55 3.65	.140 .144
ØS	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

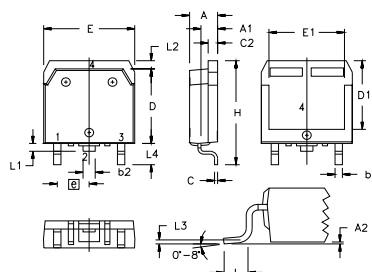
TO-3P (IXTQ) Outline



1 - GATE
2 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)
4 - DRAIN (COLLECTOR)

SYM	INCHES	MILLIMETERS
	MIN MAX	MIN MAX
A	.185 .193	4.70 4.90
A ₁	.051 .059	1.30 1.50
A ₂	.057 .065	1.45 1.65
b	.035 .045	0.90 1.15
b ₂	.075 .087	1.90 2.20
b ₄	.114 .126	2.90 3.20
c	.022 .031	0.55 0.80
D	.780 .799	19.80 20.30
D ₁	.665 .677	16.90 17.20
E	.610 .622	15.50 15.80
E ₁	.531 .539	13.50 13.70
e	.215 BSC	5.45 BSC
L	.779 .795	19.80 20.20
L ₁	.134 .142	3.40 3.60
ØP	.126 .134	3.20 3.40
ØP ₁	.272 .280	6.90 7.10
S	.193 .201	4.90 5.10

TO-268 (IXTT) Outline



SYM	INCHES	MILLIMETERS
	MIN MAX	MIN MAX
A	.193 .201	4.90 5.10
A ₁	.106 .114	2.70 2.90
A ₂	.001 .010	0.02 0.25
b	.045 .057	1.15 1.45
b ₂	.075 .083	1.90 2.10
C	.016 .026	0.40 0.65
C ₂	.057 .063	1.45 1.60
D	.543 .551	13.80 14.00
D ₁	.488 .500	12.40 12.70
E	.624 .632	15.85 16.05
E ₁	.524 .535	13.30 13.60
e	.215 BSC	5.45 BSC
H	.736 .752	18.70 19.10
L	.094 .106	2.40 2.70
L ₁	.047 .055	1.20 1.40
L ₂	.039 .045	1.00 1.15
L ₃	.010 BSC	0.25 BSC
L ₄	.150 .161	3.80 4.10

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

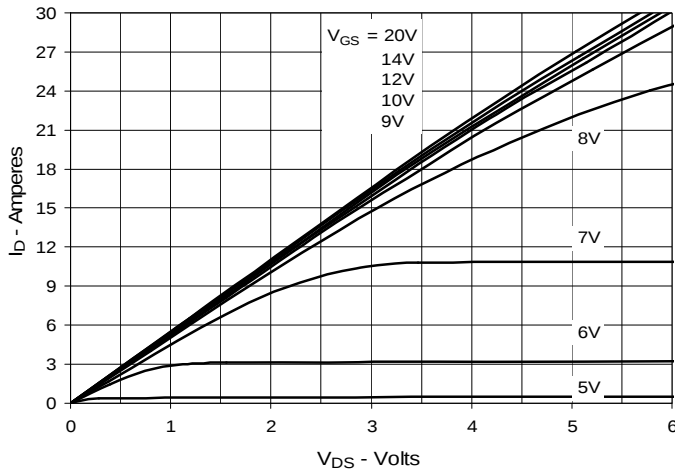


Fig. 2. Extended Output Characteristics
@ 25°C

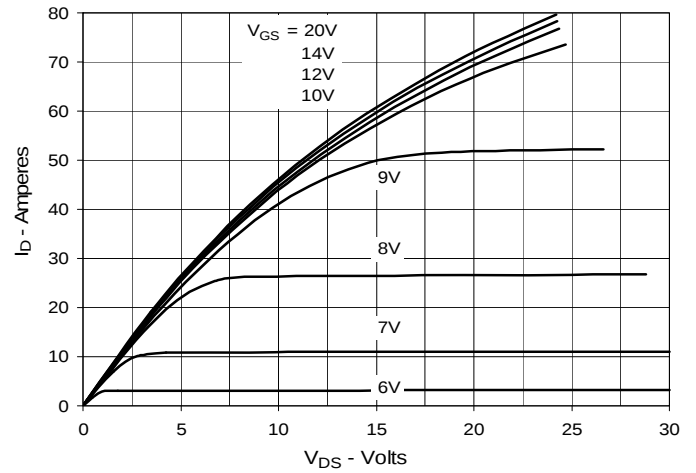


Fig. 3. Output Characteristics
@ 125°C

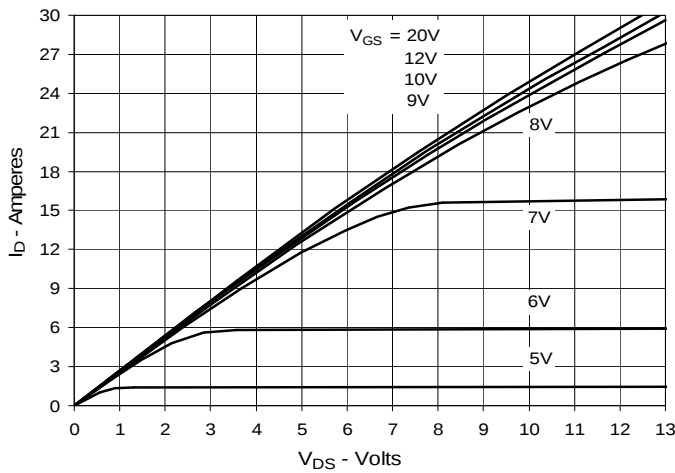


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 15A$ Value
vs. Junction Temperature

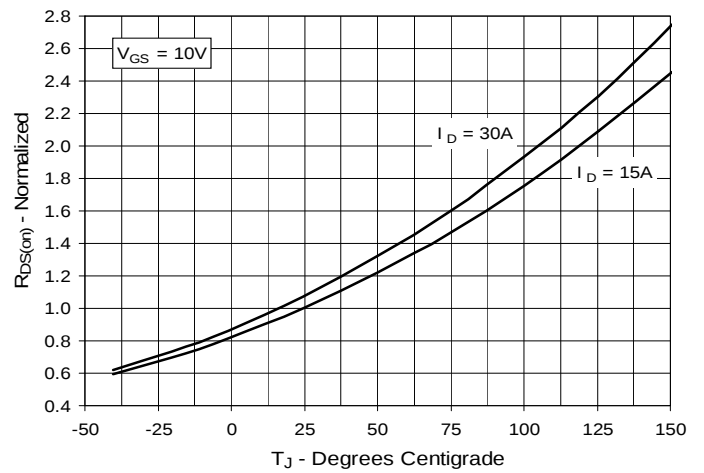


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 15A$ Value
vs. Drain Current

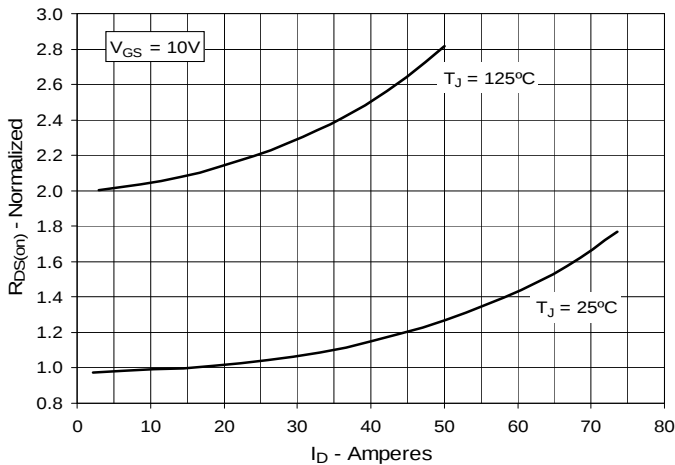


Fig. 6. Maximum Drain Current vs.
Case Temperature

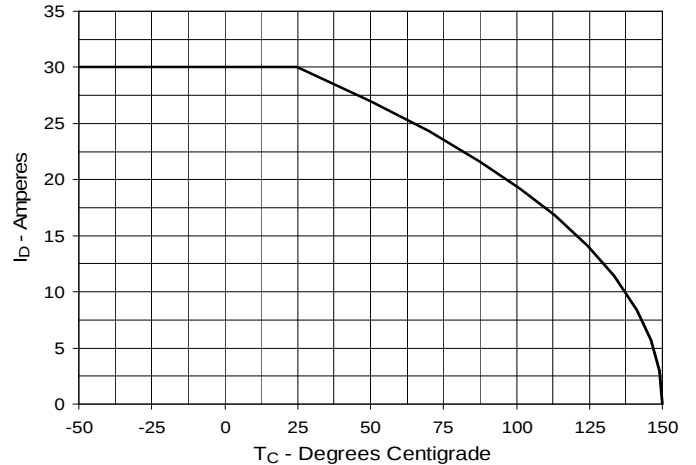


Fig. 7. Input Admittance

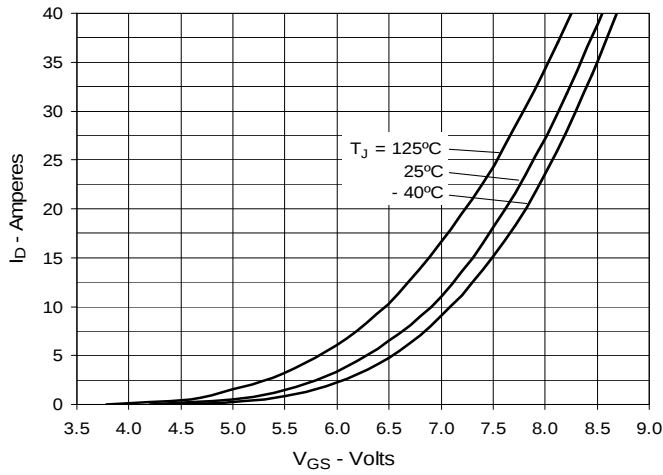


Fig. 8. Transconductance

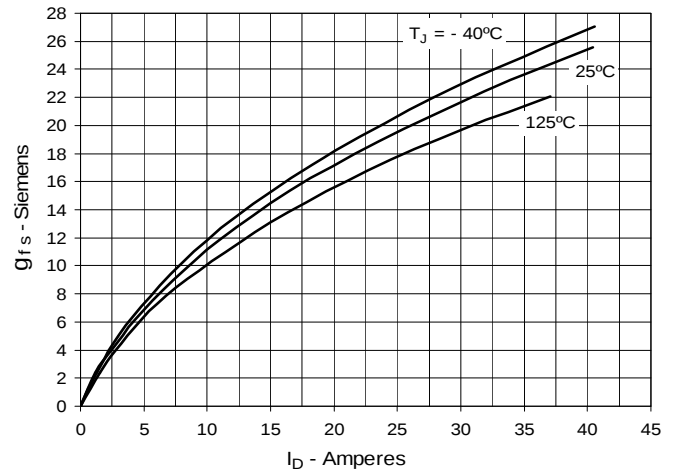


Fig. 9. Forward Voltage Drop of Intrinsic Diode

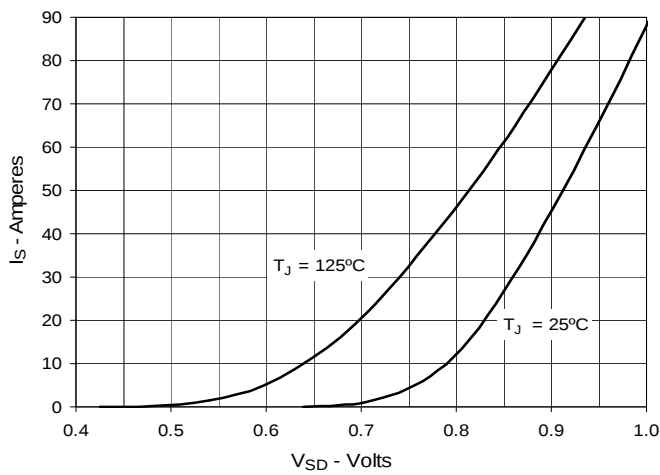


Fig. 10. Gate Charge

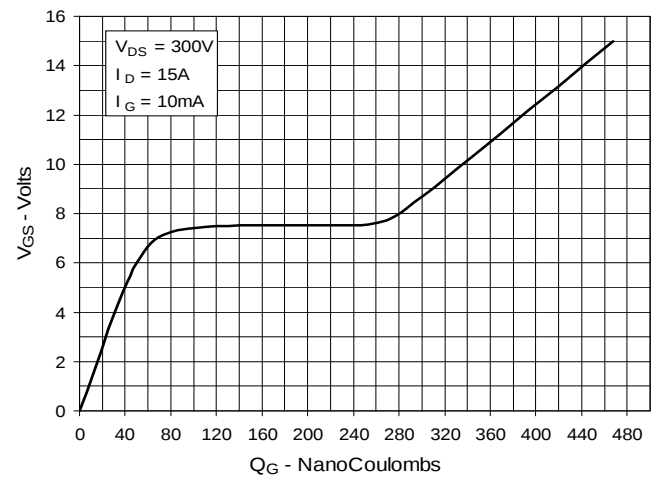


Fig. 11. Capacitance

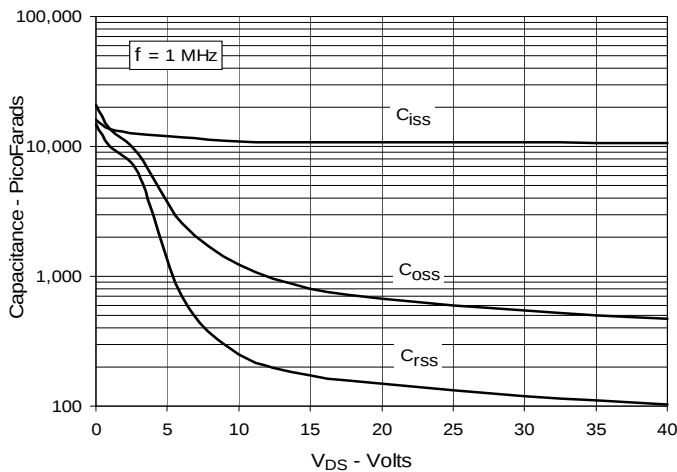


Fig. 12. Maximum Transient Thermal Impedance

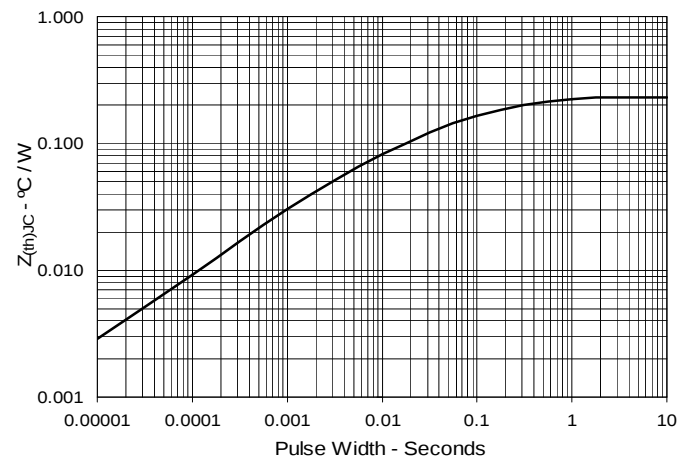


Fig. 13. Forward-Bias Safe Operating Area

@ $T_C = 25^\circ\text{C}$

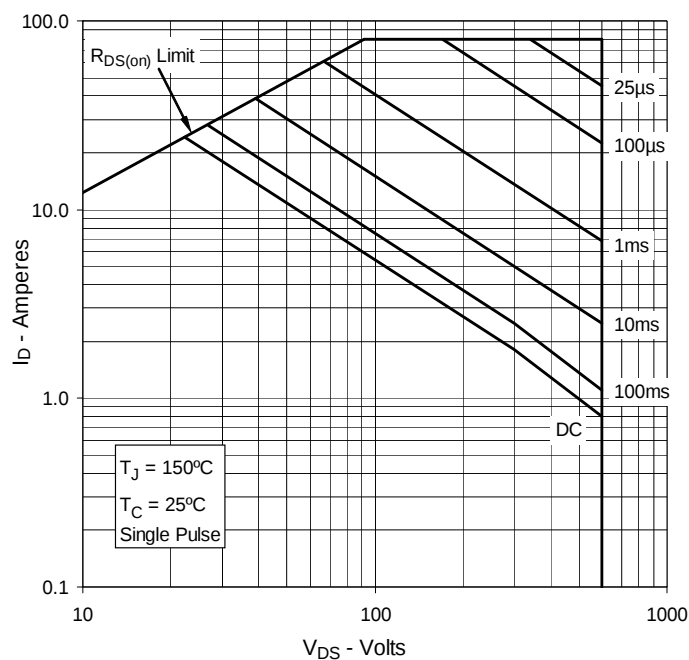
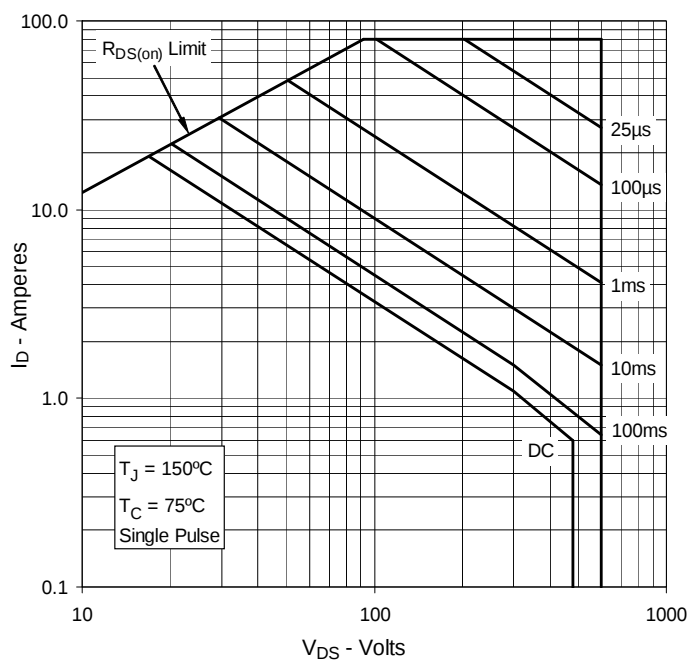


Fig. 14. Forward-Bias Safe Operating Area

@ $T_C = 75^\circ\text{C}$





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